

Product Summary

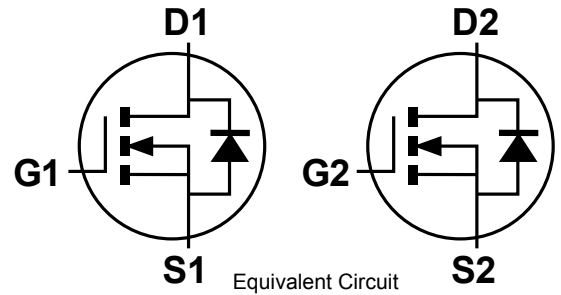
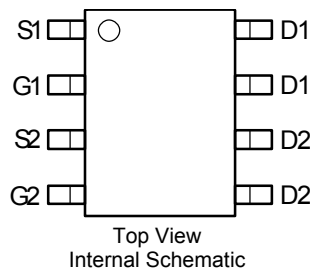
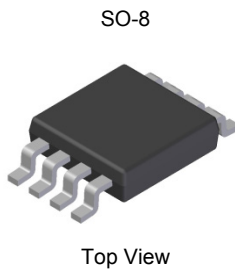
$V_{(BR)DSS}$	$R_{DS(ON) MAX}$	I_D $T_A = +25^{\circ}C$
40V	24m Ω @ $V_{GS} = 10V$	9.0A
	32m Ω @ $V_{GS} = 4.5V$	7.8A

Description

This new generation MOSFET has been designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Motor Control
- Backlighting
- Power Management Functions
- DC-DC Converters



Features

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 standards for High Reliability**

Mechanical Data

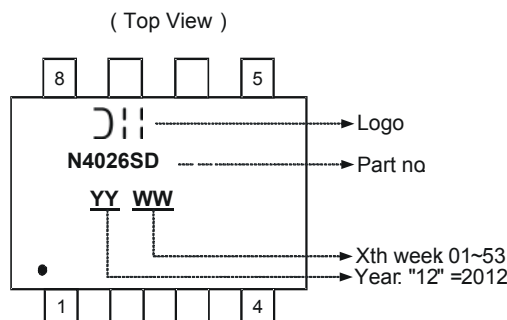
- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See diagram below
- Terminals: Finish — Matte Tin annealed over Copper lead frame. Solderable per MIL-STD-202, Method 208 (e3)
- Weight: 0.074 grams (approximate)

Ordering Information (Note 4 & 5)

Part Number	Compliance	Case	Packaging
DMN4026SSD-13	Standard	SO-8	2,500/Tape & Reel
DMN4026SSDQ-13	Automotive	SO-8	2,500/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_grade_definitions/.
 5. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	40	V
Gate-Source Voltage			V_{GSS}	± 20	V
Continuous Drain Current (Note 7) $V_{GS} = 10\text{V}$	Steady State	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	I_D	7.0 5.6	A
	$T < 10\text{s}$	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	I_D	9.0 7.2	A
Maximum Continuous Body Diode Forward Current (Note 7)			I_S	2.5	A
Pulsed Drain Current (10 μs pulse, duty cycle = 1%)			I_{DM}	70	A

Thermal Characteristics

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 6)	$T_A = +25^\circ\text{C}$	P_D	1.3	W
	$T_A = +70^\circ\text{C}$		0.8	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	98	$^\circ\text{C/W}$
	$t < 10\text{s}$		59	
Total Power Dissipation (Note 7)	$T_A = +25^\circ\text{C}$	P_D	1.8	W
	$T_A = +70^\circ\text{C}$		1.1	
Thermal Resistance, Junction to Ambient (Note 7)	Steady State	$R_{\theta JA}$	71	$^\circ\text{C/W}$
	$t < 10\text{s}$		43	
Thermal Resistance, Junction to Case (Note 7)		$R_{\theta JC}$	11.8	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	40	—	—	V	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	μA	$V_{DS} = 40\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	I_{GSS}	—	—	± 100	nA	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(th)}$	1	—	3	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(on)}$	—	15	24	m Ω	$V_{GS} = 10\text{V}, I_D = 6\text{A}$
		—	20	32		$V_{GS} = 4.5\text{V}, I_D = 5\text{A}$
Diode Forward Voltage	V_{SD}	—	0.7	1.0	V	$V_{GS} = 0\text{V}, I_S = 1.0\text{A}$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	—	1060	—	pF	$V_{DS} = 20\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$
Output Capacitance	C_{oss}	—	84	—		
Reverse Transfer Capacitance	C_{rss}	—	58	—		
Gate Resistance	R_G	—	1.6	—	Ω	$V_{DS} = 0\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$
Total Gate Charge ($V_{GS} = 4.5\text{V}$)	Q_g	—	8.8	20	nC	$V_{DS} = 20\text{V}, I_D = 8\text{A}$
Total Gate Charge ($V_{GS} = 10\text{V}$)	Q_g	—	19.1	43		
Gate-Source Charge	Q_{gs}	—	3.0	7.5		
Gate-Drain Charge	Q_{gd}	—	2.5	6		
Turn-On Delay Time	$t_{D(on)}$	—	5.3	—	nS	$V_{DD} = 25\text{V}, R_L = 2.5\Omega$ $V_{GS} = 10\text{V}, R_G = 3\Omega$
Turn-On Rise Time	t_r	—	7.1	—		
Turn-Off Delay Time	$t_{D(off)}$	—	15.1	—		
Turn-Off Fall Time	t_f	—	4.8	—		
Body Diode Reverse Recovery Time	t_{rr}	—	10.5	—	nS	$I_F = 8\text{A}, di/dt = 100\text{A}/\mu\text{s}$
Body Diode Reverse Recovery Charge	Q_{rr}	—	4.15	—	nC	$I_F = 8\text{A}, di/dt = 100\text{A}/\mu\text{s}$

- Notes:
6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 7. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 8. Short duration pulse test used to minimize self-heating effect.
 9. Guaranteed by design. Not subject to product testing.

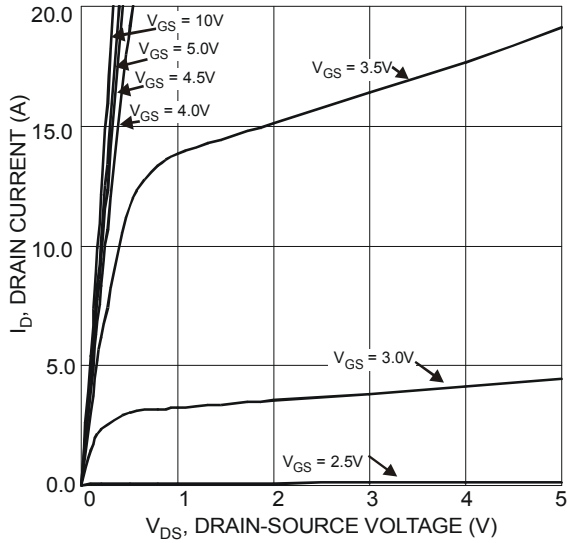


Figure 1 Typical Output Characteristic

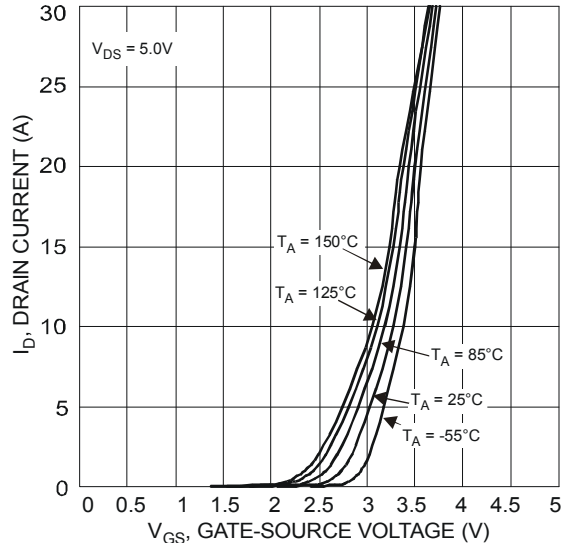


Figure 2 Typical Transfer Characteristics

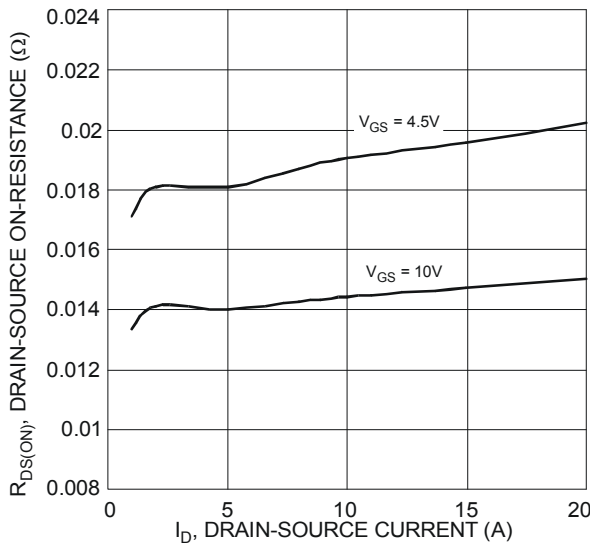


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

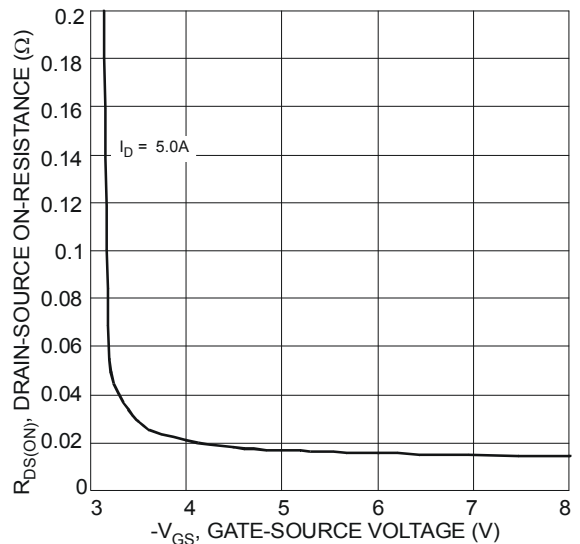


Figure 4 Typical Transfer Characteristic

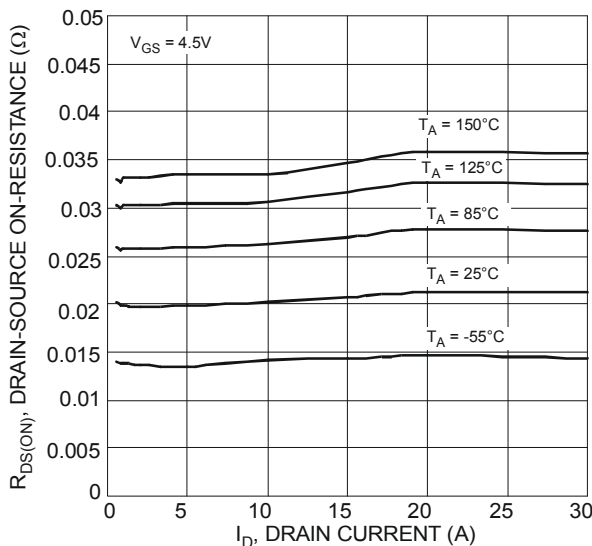


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

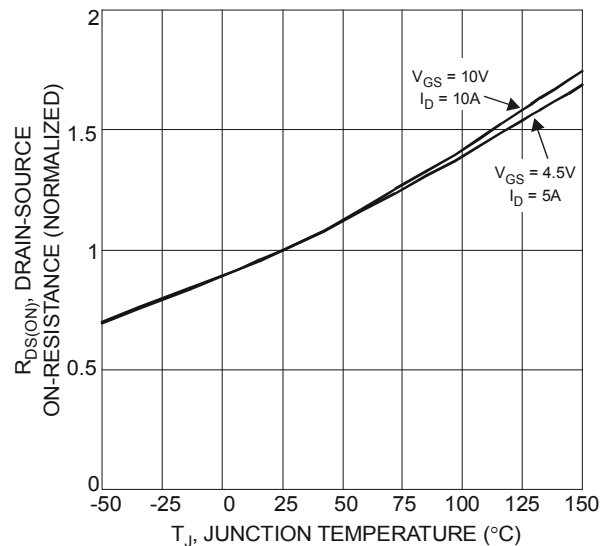


Figure 6 On-Resistance Variation with Temperature

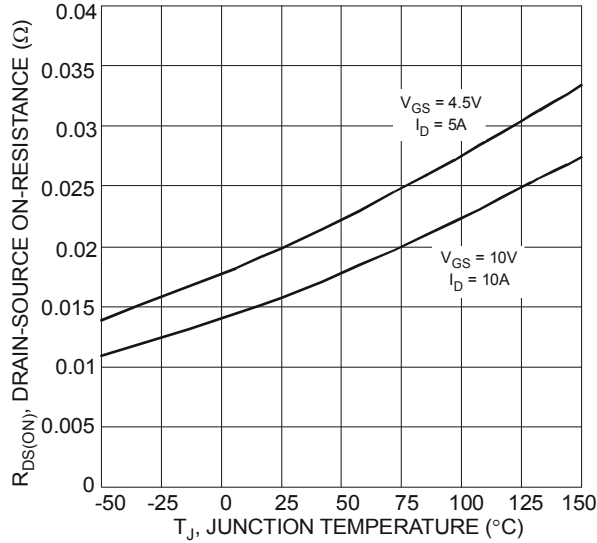


Figure 7 On-Resistance Variation with Temperature

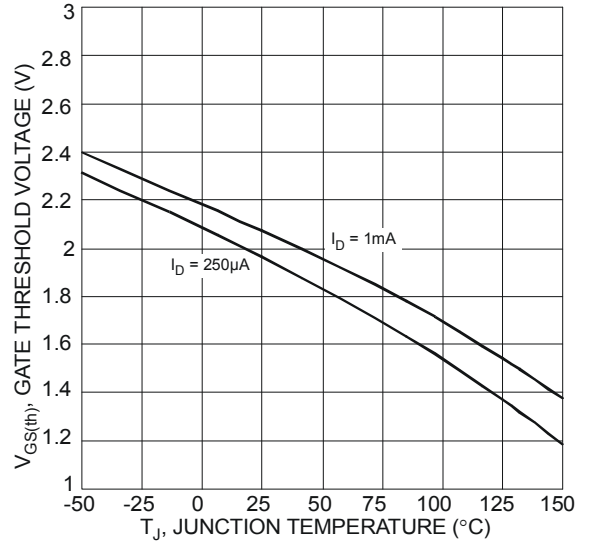


Figure 8 Gate Threshold Variation vs. Ambient Temperature

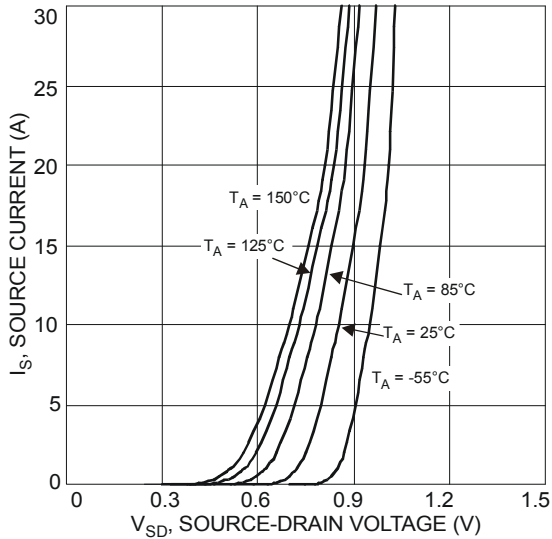


Figure 9 Diode Forward Voltage vs. Current

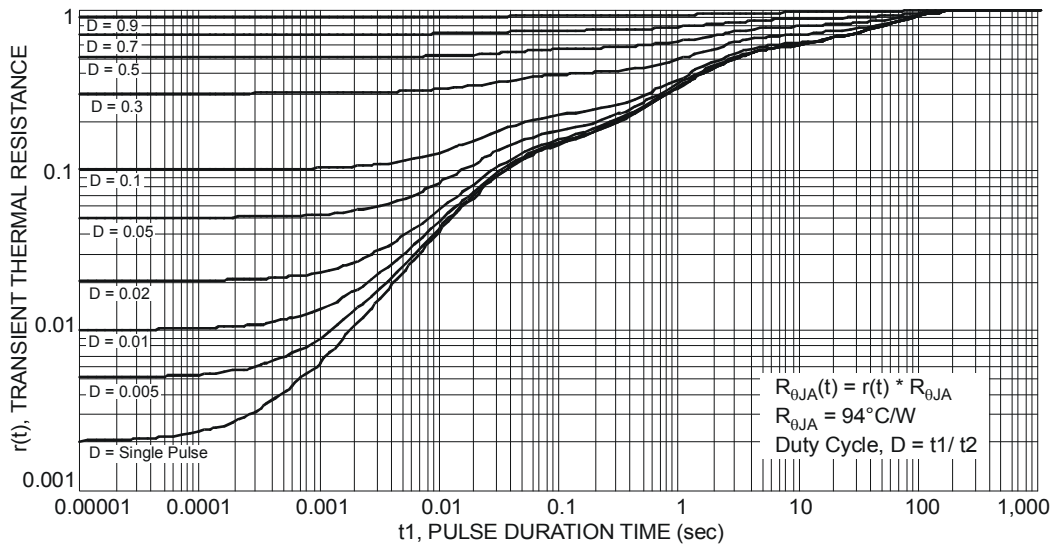
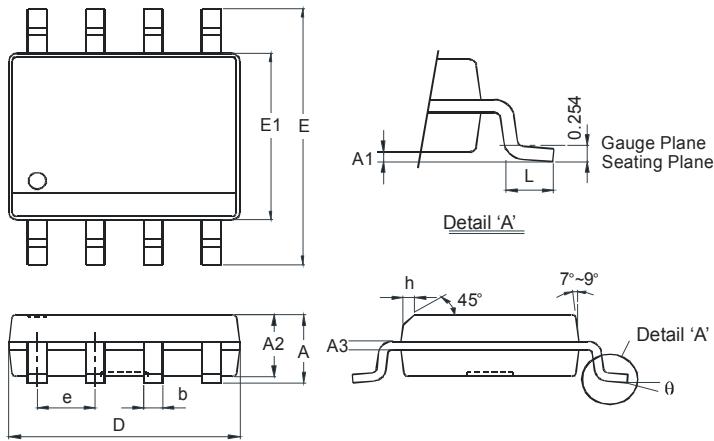


Figure 10 Transient Thermal Resistance

Package Outline Dimensions

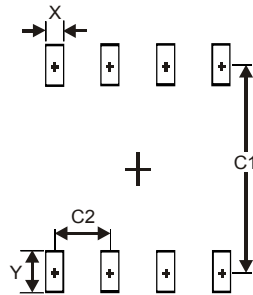
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



SO-8		
Dim	Min	Max
A	-	1.75
A1	0.10	0.20
A2	1.30	1.50
A3	0.15	0.25
b	0.3	0.5
D	4.85	4.95
E	5.90	6.10
E1	3.85	3.95
e	1.27 Typ	
h	-	0.35
L	0.62	0.82
θ	0°	8°
All Dimensions in mm		

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for latest version.



Dimensions	Value (in mm)
X	0.60
Y	1.55
C1	5.4
C2	1.27

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